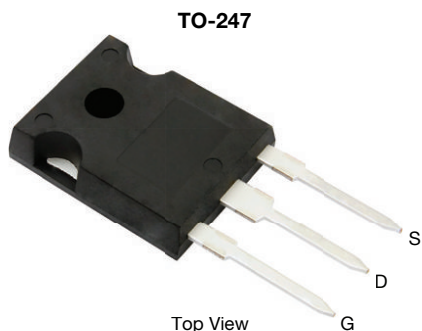


N-Channel 200 V (D-S) 175 °C MOSFET



FEATURES

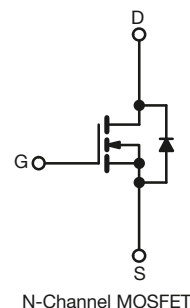
- ThunderFET® power MOSFET
- Low R_{DS} - Q_g figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Power supplies
- DC/AC inverter
- DC/DC converter
- Solar micro inverter
- Motor drive switch



PRODUCT SUMMARY

V_{DS} (V)	200
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0095
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5$ V	0.0104
Q_g typ. (nC)	86
I_D (A)	100 ^d
Configuration	Single

ORDERING INFORMATION

Package	TO-247
Lead (Pb)-free and halogen-free	SUG90090E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	200	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	100 ^d	A
		77.6	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	300	
Continuous source-drain diode current	I_S	100 ^d	
Single pulse avalanche current ^a	I_{AS}	100	mJ
Single pulse avalanche energy ^a	E_{AS}	500	
Maximum power dissipation	P_D	395 ^b	W
		132 ^b	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) ^c	R_{thJA}	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.38	

Notes

- Duty cycle ≤ 1 %
- See SOA curve for voltage derating
- When mounted on 1" square PCB (FR4 material)
- Package limited

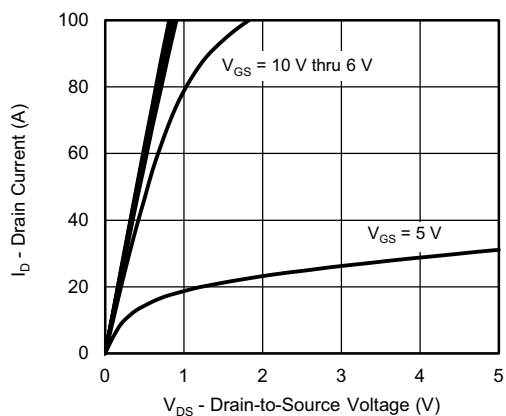
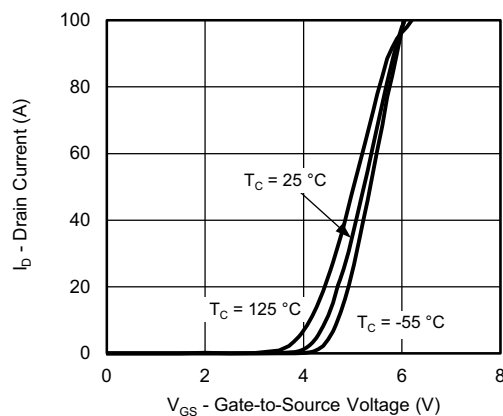
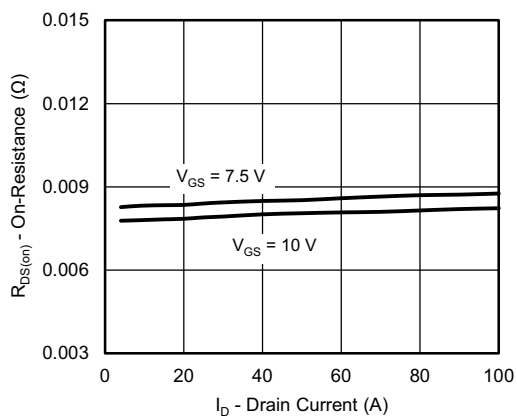
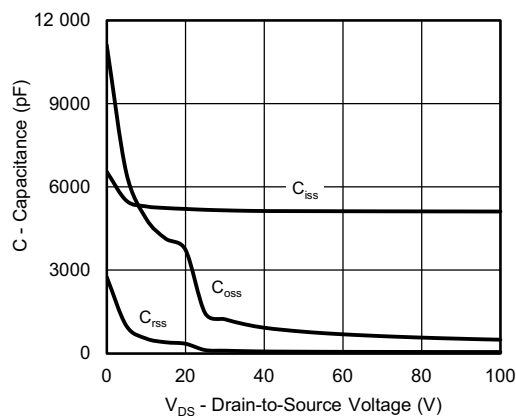
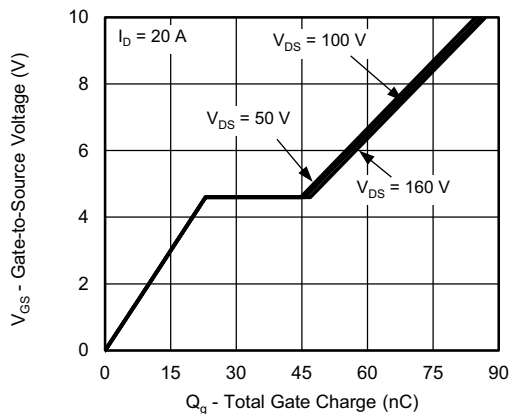
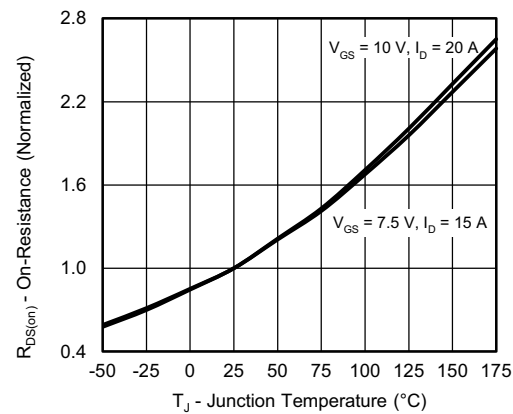


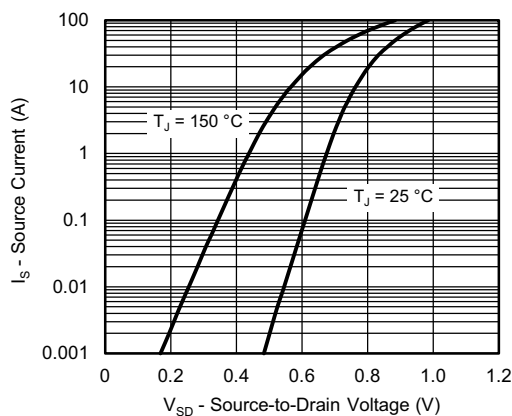
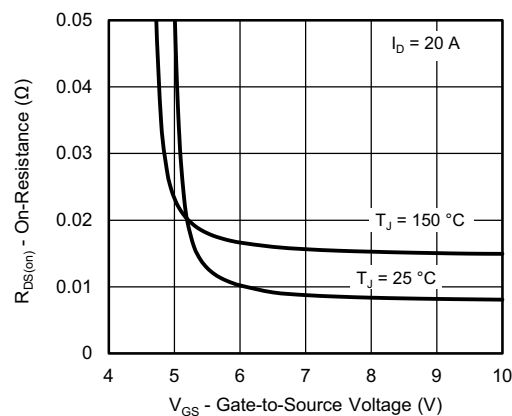
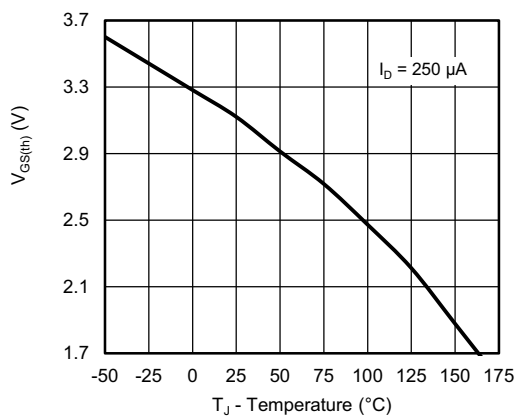
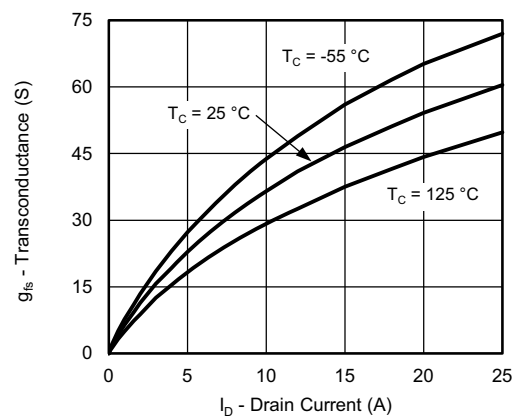
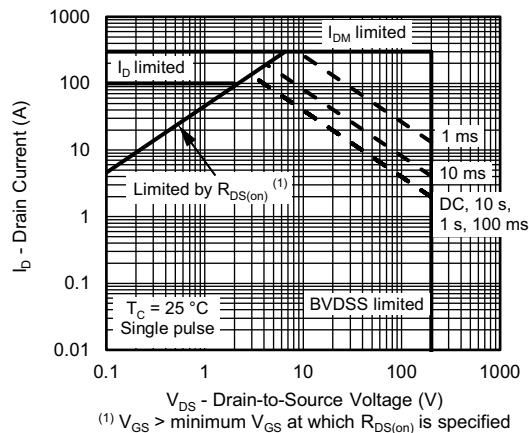
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	200	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	250	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.0079	0.0095	Ω
		V _{GS} = 7.5 V, I _D = 15 A	-	0.0083	0.0104	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A	-	54	-	S
Dynamic ^b						
Input capacitance	C _{iSS}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	-	5220	-	pF
Output capacitance	C _{oss}		-	495	-	
Reverse transfer capacitance	C _{rSS}		-	51	-	
Total gate charge	Q _g	V _{DS} = 100 V, V _{GS} =10 V, I _D = 20 A	-	86	129	nC
Gate-source charge	Q _{gs}		-	23	-	
Gate-drain charge	Q _{gd}		-	22.7	-	
Gate resistance	R _g	f = 1 MHz	0.6	3.2	14.4	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = 100 V, R _L = 6.7 Ω, I _D ≅ 15 A, V _{GEN} = 10 V, R _g = 1 Ω	-	18	27	ns
Rise time	t _r		-	44	66	
Turn-off delay time	t _{d(off)}		-	60	90	
Fall time	t _f		-	40	60	
Drain-Source Body Diode Characteristics						
Pulse diode forward current (t = 100 μs)	I _{SM}		-	-	100	A
Body diode voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs	-	146	220	ns
Body diode reverse recovery charge	Q _{rr}		-	0.91	1.37	μC
Reverse recovery fall time	t _a		-	115	-	ns
Reverse recovery rise time	t _b		-	31	-	
Body diode peak reverse recovery charge	I _{RM(REC)}		-	12	18	A

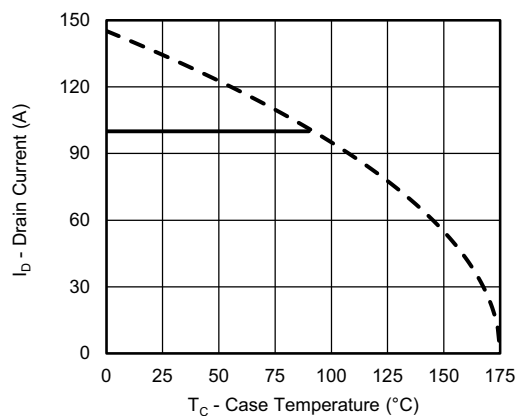
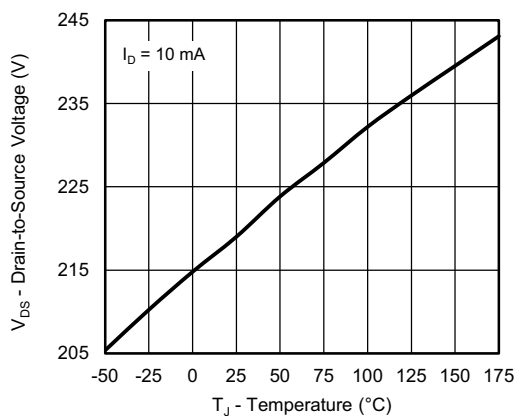
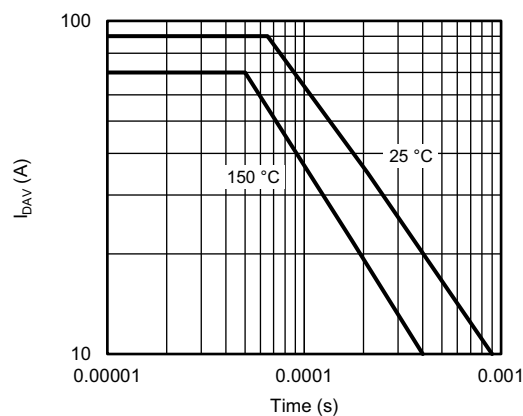
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

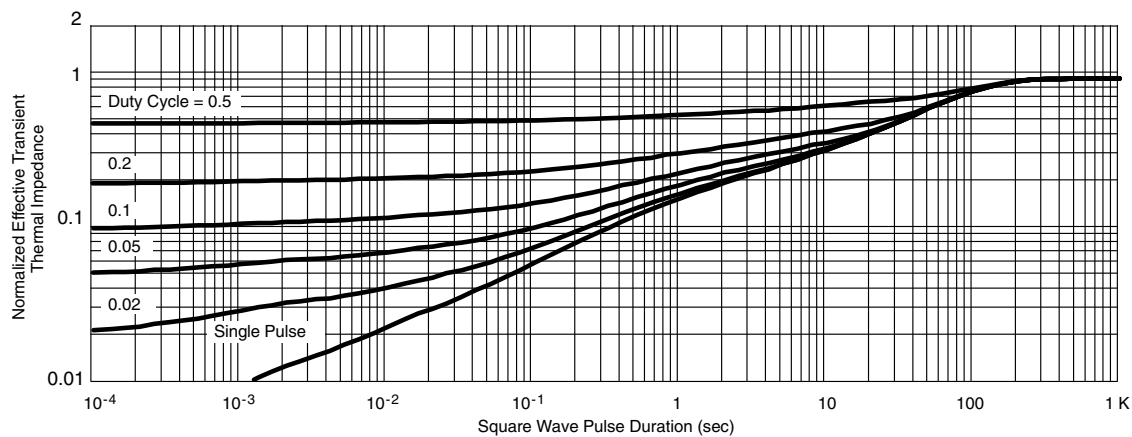
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Transconductance

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Drain Source Breakdown vs. Junction Temperature

 I_{DAV} vs. Time
Note

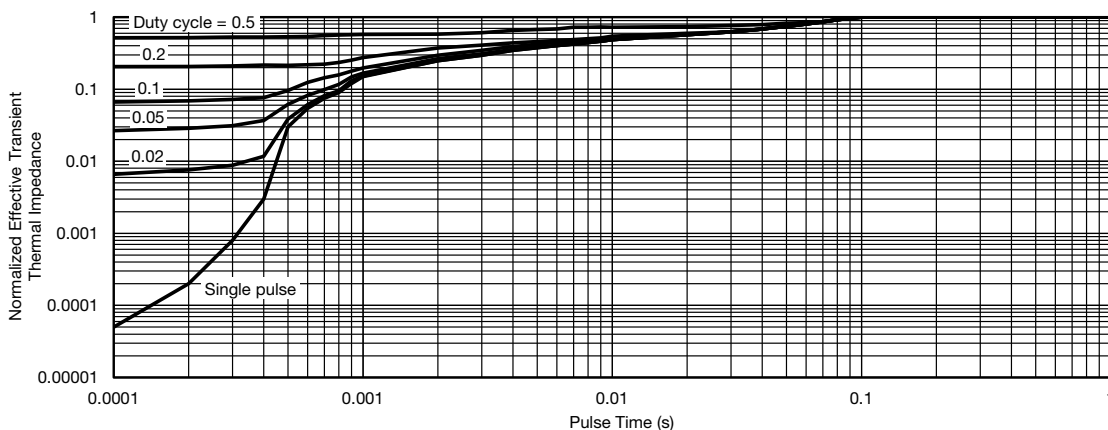
- a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9



MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
A	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
c	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

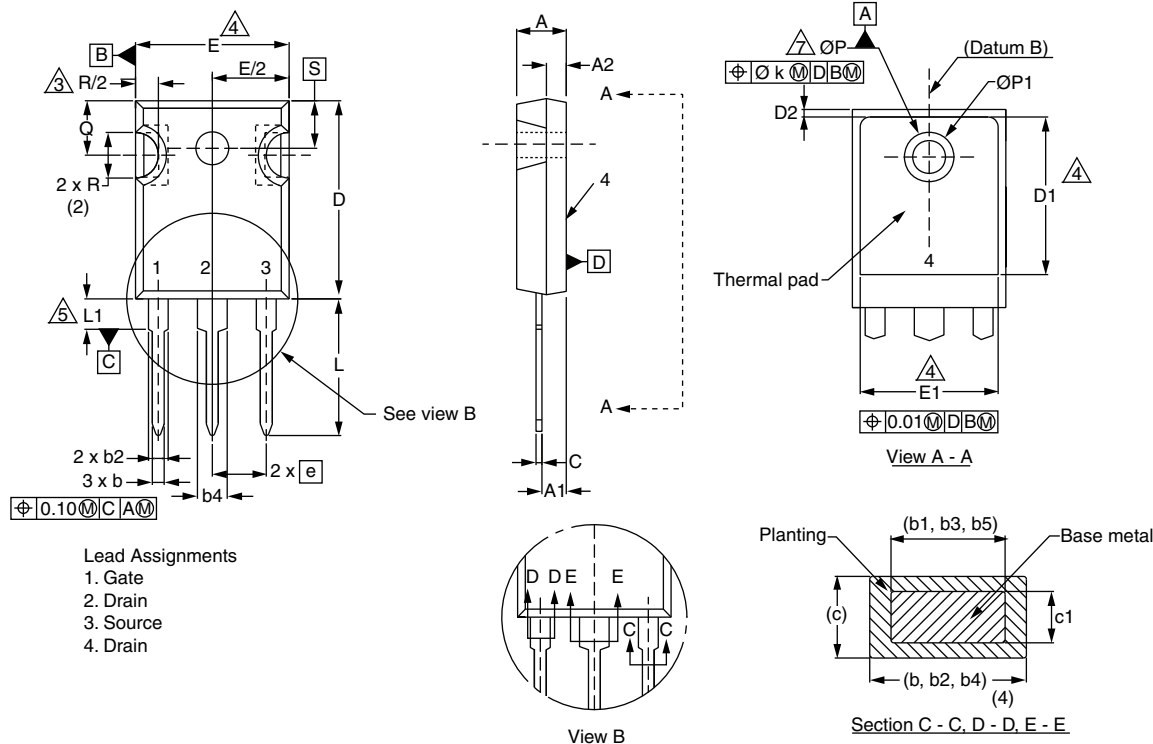
MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
e	5.44 BSC		
L	14.90	15.40	
L1	3.96	4.16	6
Ø P	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

Notes

- Package reference: JEDEC® TO247, variation AC
- All dimensions are in mm
- Slot required, notch may be rounded
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



VERSION 2: FACILITY CODE = Y



MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

MILLIMETERS			
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E19-0614-Rev. E, 08-Jan-2020
 DWG: 5971

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



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